

IN THE SPECIFICATION:

Please amend paragraph [0018] as follows:

[0018] FIGs. 3A and 3B ~~illustrates~~ illustrate exemplary electron beam lithography systems of the present invention that may be used to implement the methods of the present invention.

Please amend paragraph [0033] as follows:

[0033] Following exposing of the non-angled features 402 in act 506, the rotational orientations of the stage 17 supporting the substrate 18 and the first aperture 30 and the second aperture 32, may be relatively altered with respect to each other by a predetermined angle. In an exemplary embodiment, the stage 17 supporting the substrate 18 may be rotated by an angle θ about a Z axis that is perpendicular to the surface of substrate 18 while the first aperture 30 and the second aperture 32 remain stationary. In another exemplary embodiment, the first aperture 30 and the second aperture 32 may be rotated by an angle θ about a Z axis that is perpendicular to the surface of substrate 18 while the substrate 18 remains stationary. The rotation of stage 17 may be controlled by the laser interferometer 28 operably coupled to the stage control circuit 7 and the processor 1 to accurately control and measure the rotation of stage 17. If the first aperture 30 and the second aperture 32 are rotated, the rotation may be similarly controlled by the laser interferometer 28' operably coupled to the aperture position control circuit 36 to accurately control and measure the position thereof, or a stepper motor or rotary encoder may be employed. In act 508, the angled features 404 may then be formed by exposing the resist to an electron beam shot-by-shot using generally rectangular-shaped shots from the EBL system. Since the substrate 18 or the first aperture 30 and the second aperture 32 ~~has~~ have been rotated, the angled features 404 are exposed on the resist by the EBL system as if they were non-angled features.